

# CSD22205L –8-V P-Channel NexFET™ Power MOSFET

## 1 Features

- Low Resistance
- Small Footprint 1.2 mm × 1.2 mm
- Low Profile 0.35-mm Height
- Lead Free
- Gate-Source Voltage Clamp
- Gate ESD Protection
- RoHS Compliant
- Halogen Free

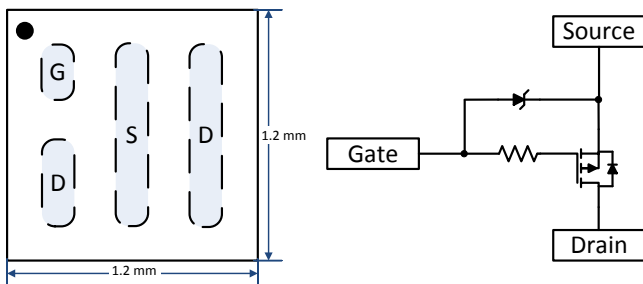
## 2 Applications

- Battery Management
- Load Switch
- Battery Protection

## 3 Description

This –8-V, 8.2-mΩ, 1.2-mm × 1.2-mm Land Grid Array (LGA) NexFET™ device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra-low profile. The Land Grid Array (LGA) package is a silicon chip scale package with metal pads instead of solder balls.

Top View and Circuit Configuration



## Product Summary

T <sub>A</sub> = 25°C		VALUE	UNIT
V <sub>DS</sub>	Drain-to-Source Voltage	–8	V
Q <sub>g</sub>	Gate Charge Total (–4.5 V)	6.5	nC
Q <sub>gd</sub>	Gate Charge Gate-to-Drain	1.0	nC
R <sub>DS(on)</sub>	Drain-to-Source On Resistance	V <sub>GS</sub> = –1.5 V	30
		V <sub>GS</sub> = –1.8 V	20
		V <sub>GS</sub> = –2.5 V	11.5
		V <sub>GS</sub> = –4.5 V	8.2
V <sub>GS(th)</sub>	Threshold Voltage	–0.7	V

## Device Information<sup>(1)</sup>

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD22205L	3000	7-Inch Reel	1.20-mm × 1.20-mm Land Grid Array Package	Tape and Reel
CSD22205LT	250			

(1) For all available packages, see the orderable addendum at the end of the data sheet.

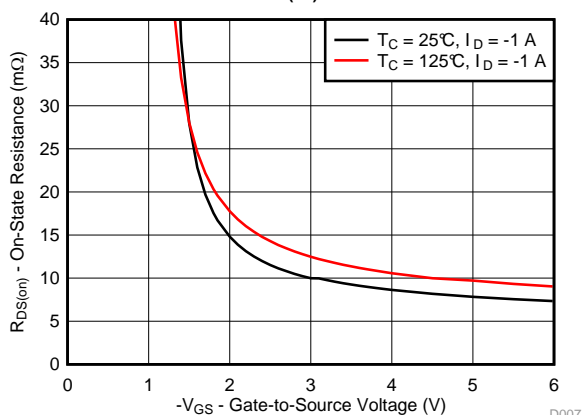
## Absolute Maximum Ratings

T <sub>A</sub> = 25°C		VALUE	UNIT
V <sub>DS</sub>	Drain-to-Source Voltage	–8	V
V <sub>GS</sub>	Gate-to-Source Voltage	–6	V
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>	–7.4	A
I <sub>DM</sub>	Pulsed Drain Current <sup>(2)</sup>	–71	A
P <sub>D</sub>	Power Dissipation <sup>(1)</sup>	0.6	W
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction Temperature, Storage Temperature	–55 to 150	°C

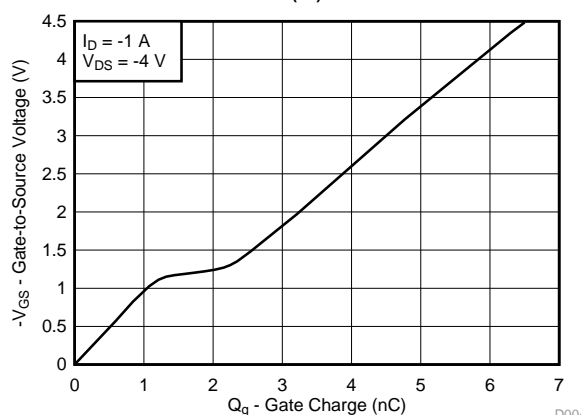
(1) Min Cu R<sub>θJA</sub> = 225°C/W.

(2) Pulse width ≤ 100 μs, duty cycle ≤ 1%.

R<sub>DS(on)</sub> vs V<sub>GS</sub>



R<sub>DS(on)</sub> vs V<sub>GS</sub>



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## 4 Revision History

DATE	REVISION	NOTES
May 2017	*	Initial release.

## 5 Specifications

### 5.1 Electrical Characteristics

 $T_A = 25^\circ\text{C}$  (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>STATIC CHARACTERISTICS</b>						
$B_{V_{DSS}}$	Drain-to-source voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-8			V
$I_{DSS}$	Drain-to-source leakage current	$V_{GS} = 0\text{ V}, V_{DS} = -6.4\text{ V}$			-100	nA
$I_{GSS}$	Gate-to-source leakage current	$V_{DS} = 0\text{ V}, V_{GS} = -6\text{ V}$			-100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.4	-0.7	-1.05	V
$R_{DS(on)}$	Drain-to-source on resistance	$V_{GS} = -1.5\text{ V}, I_D = -0.2\text{ A}$		30		m $\Omega$
		$V_{GS} = -1.8\text{ V}, I_D = -1\text{ A}$		20	40	
		$V_{GS} = -2.5\text{ V}, I_D = -1\text{ A}$		11.5	15.0	
		$V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}$		8.2	9.9	
$g_{fs}$	Transconductance	$V_{DS} = -0.8\text{ V}, I_D = -1\text{ A}$		10.4		S
<b>DYNAMIC CHARACTERISTICS</b>						
$C_{ISS}$	Input capacitance	$V_{GS} = 0\text{ V}, V_{DS} = -4\text{ V}, f = 1\text{ MHz}$		1070	1390	pF
$C_{OSS}$	Output capacitance			560	730	pF
$C_{RSS}$	Reverse transfer capacitance			190	250	pF
$R_G$	Series gate resistance			30		$\Omega$
$Q_g$	Gate charge total (-4.5 V)	$V_{DS} = -4\text{ V}, I_D = -1\text{ A}$		6.5	8.5	nC
$Q_{gd}$	Gate charge gate-to-drain			1.0		nC
$Q_{gs}$	Gate charge gate-to-source			1.2		nC
$Q_{g(th)}$	Gate charge at $V_{th}$			0.7		nC
$Q_{OSS}$	Output charge	$V_{DS} = -4\text{ V}, V_{GS} = 0\text{ V}$		4.1		nC
$t_{d(on)}$	Turnon delay time	$V_{DS} = -4\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}, R_G = 0\ \Omega$		30		$\mu\text{s}$
$t_r$	Rise time			14		$\mu\text{s}$
$t_{d(off)}$	Turnoff delay time			70		$\mu\text{s}$
$t_f$	Fall time			32		$\mu\text{s}$
<b>DIODE CHARACTERISTICS</b>						
$V_{SD}$	Diode forward voltage	$I_S = -1\text{ A}, V_{GS} = 0\text{ V}$	-0.68		-1.0	V
$Q_{rr}$	Reverse recovery charge	$V_{DS} = -4\text{ V}, I_F = -1\text{ A}, di/dt = 200\text{ A}/\mu\text{s}$		16		nC
$t_{rr}$	Reverse recovery time			38		ns

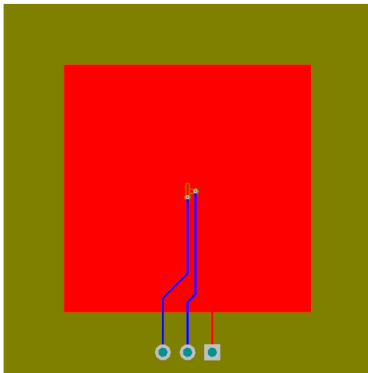
### 5.2 Thermal Information

 $T_A = 25^\circ\text{C}$  (unless otherwise stated)

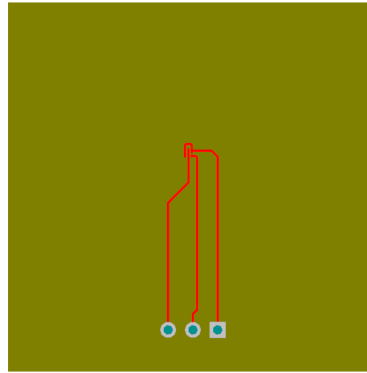
THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance <sup>(1)</sup>		75		$^\circ\text{C}/\text{W}$
	Junction-to-ambient thermal resistance <sup>(2)</sup>		225		

(1) Device mounted on FR4 material with 1-in<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz (0.071-mm) thick Cu.

(2) Device mounted on FR4 material with minimum Cu mounting area.



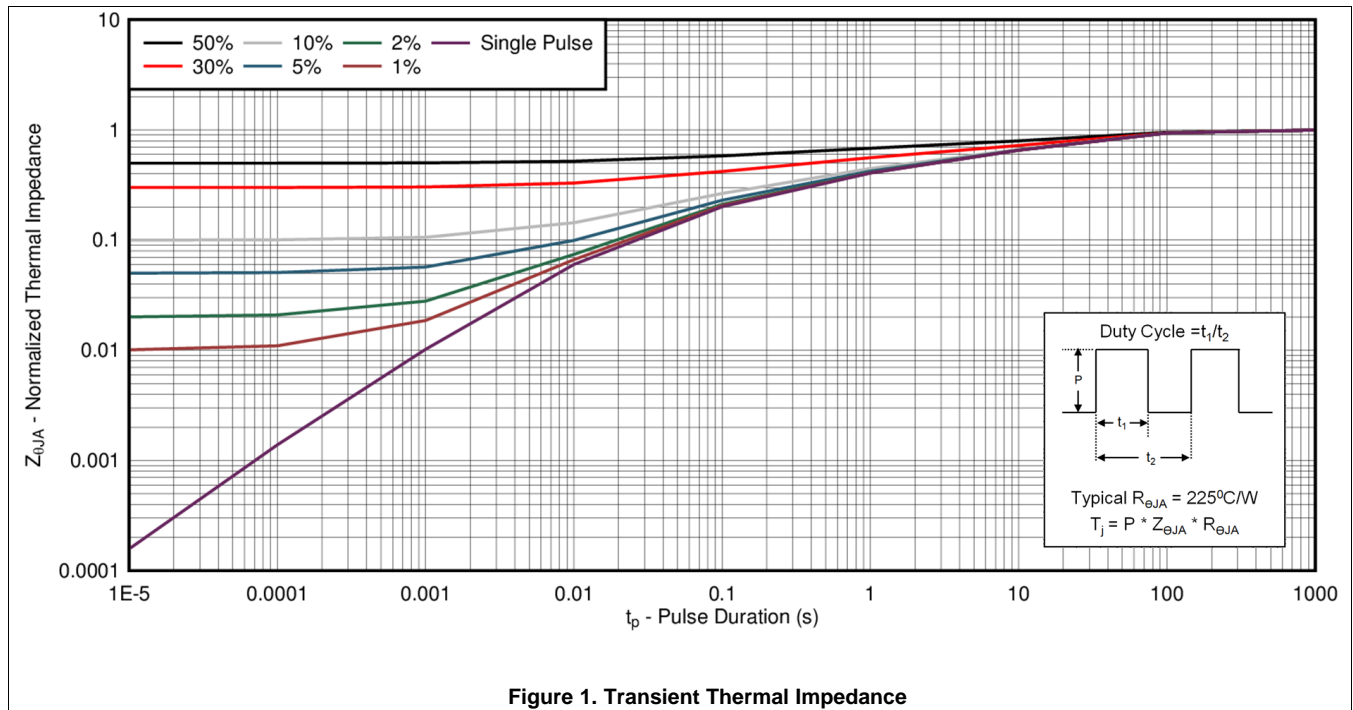
Typ  $R_{\theta JA} = 75^{\circ}\text{C/W}$   
when mounted on 1 in<sup>2</sup>  
of 2-oz Cu.



Typ  $R_{\theta JA} = 225^{\circ}\text{C/W}$   
when mounted on  
minimum pad area  
of 2-oz Cu.

### 5.3 Typical MOSFET Characteristics

$T_A = 25^{\circ}\text{C}$  (unless otherwise stated)



Typical MOSFET Characteristics (continued)

T<sub>A</sub> = 25°C (unless otherwise stated)

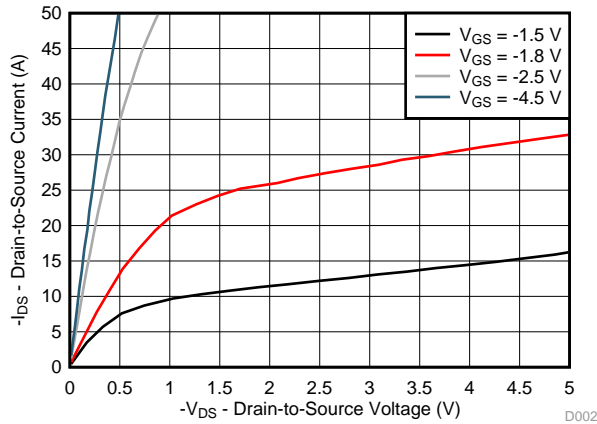


Figure 2. Saturation Characteristics

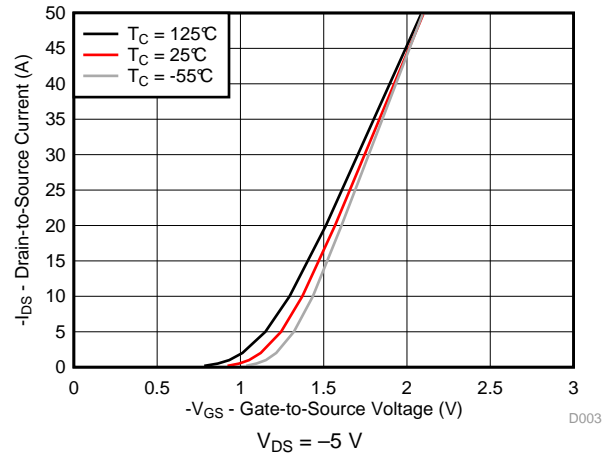


Figure 3. Transfer Characteristics

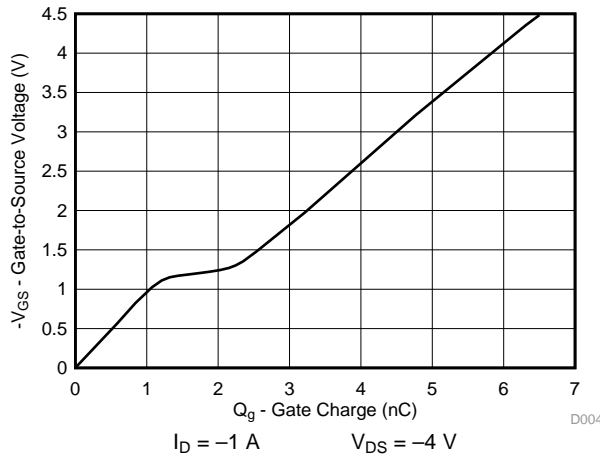


Figure 4. Gate Charge

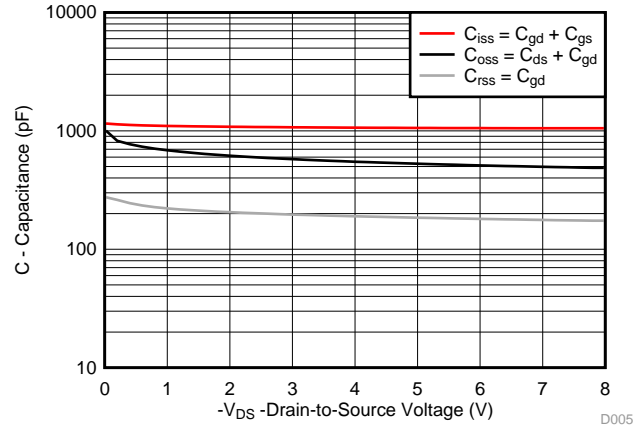


Figure 5. Capacitance

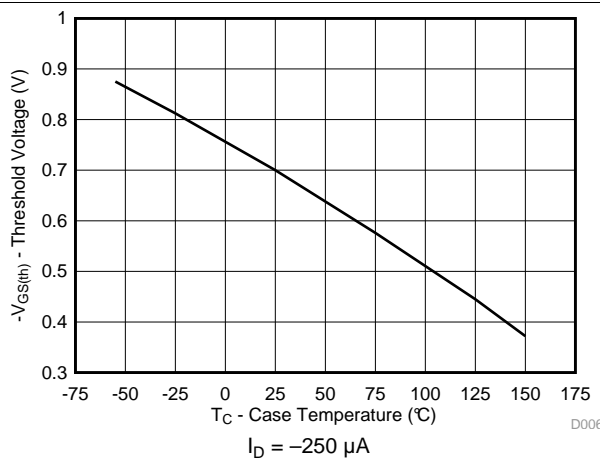


Figure 6. Threshold Voltage vs Temperature

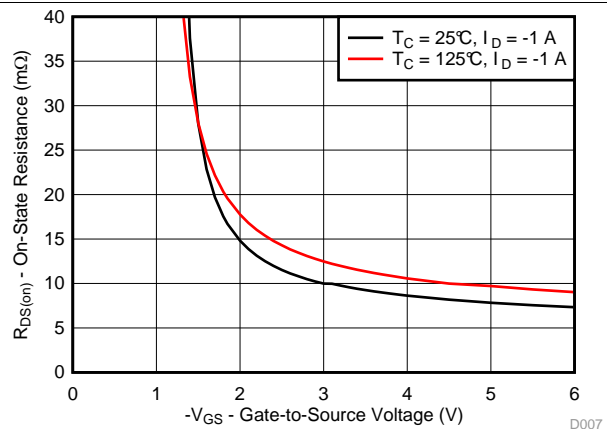


Figure 7. On-State Resistance vs Gate-to-Source Voltage

Typical MOSFET Characteristics (continued)

$T_A = 25^\circ\text{C}$  (unless otherwise stated)

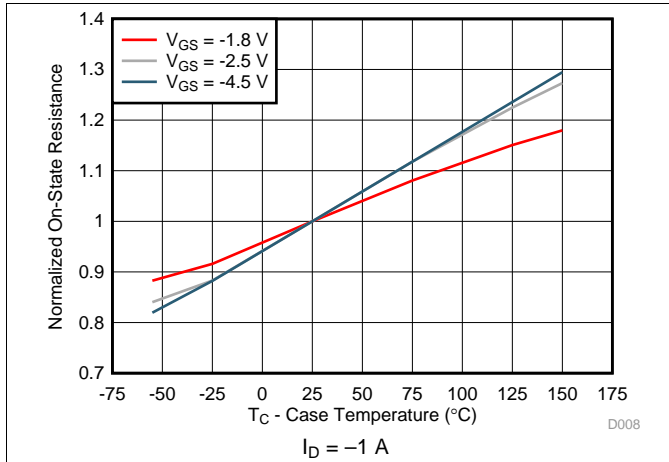


Figure 8. Normalized On-State Resistance vs Temperature

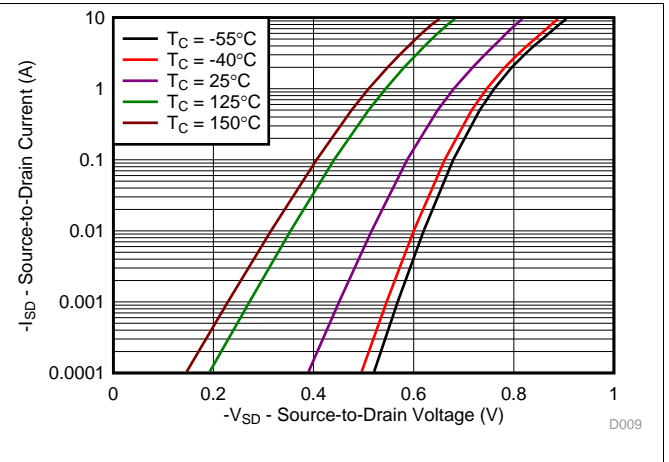


Figure 9. Typical Diode Forward Voltage

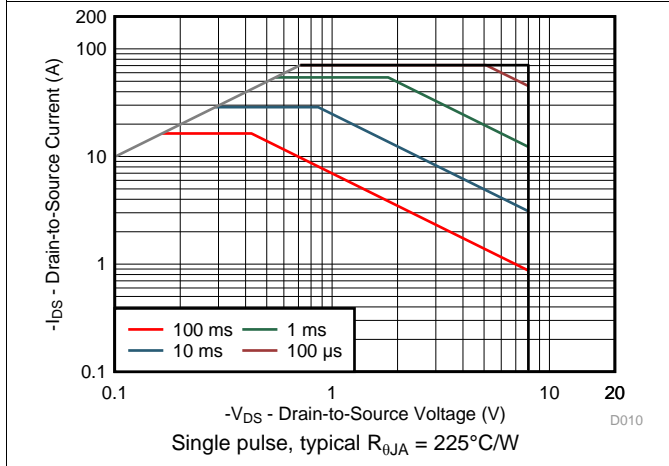


Figure 10. Maximum Safe Operating Area

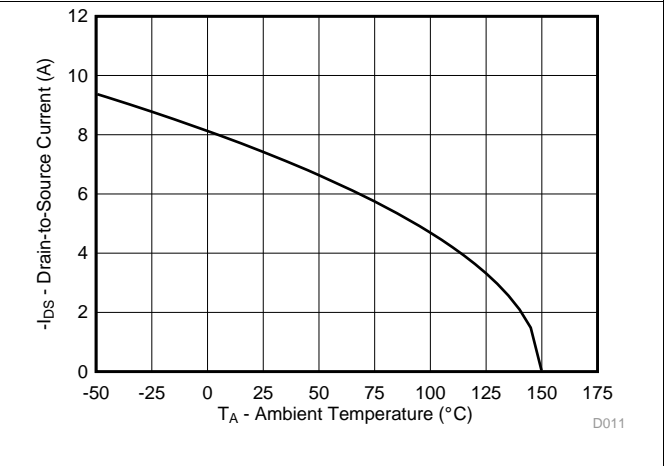


Figure 11. Maximum Drain Current vs Temperature

## 6 Device and Documentation Support

### 6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 6.3 Trademarks

NexFET, E2E are trademarks of Texas Instruments.  
All other trademarks are the property of their respective owners.

### 6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 6.5 Glossary

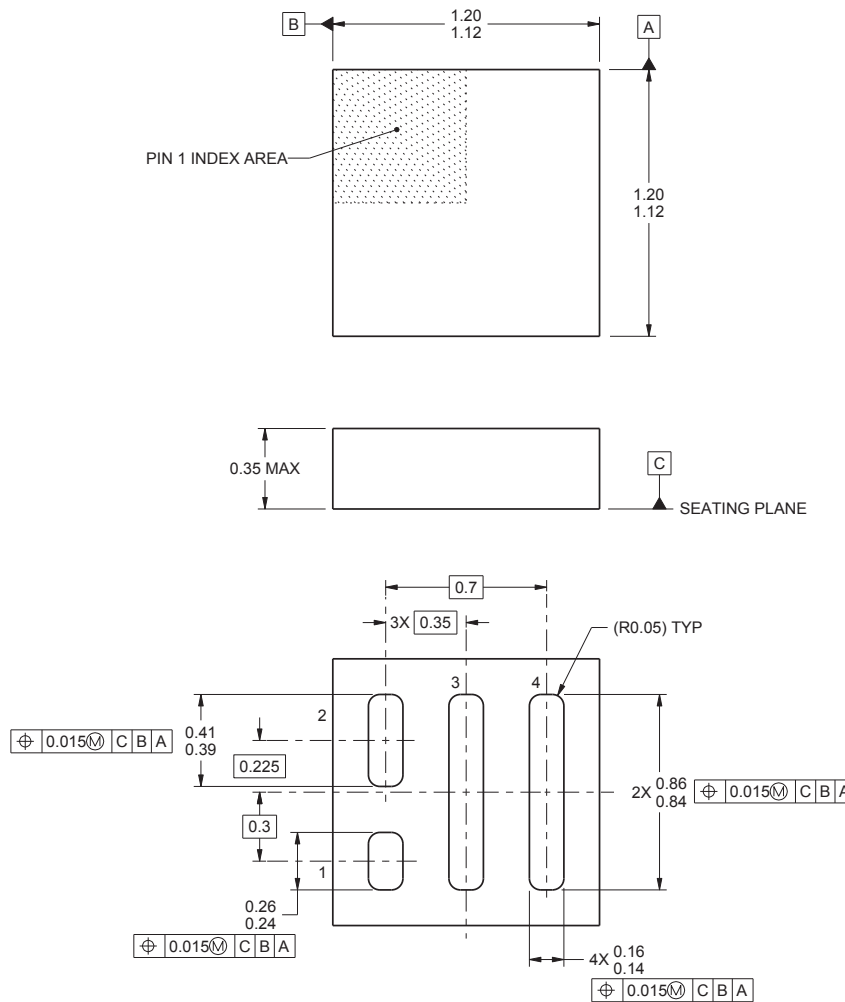
[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

### 7.1 CSD22205L Package Dimensions



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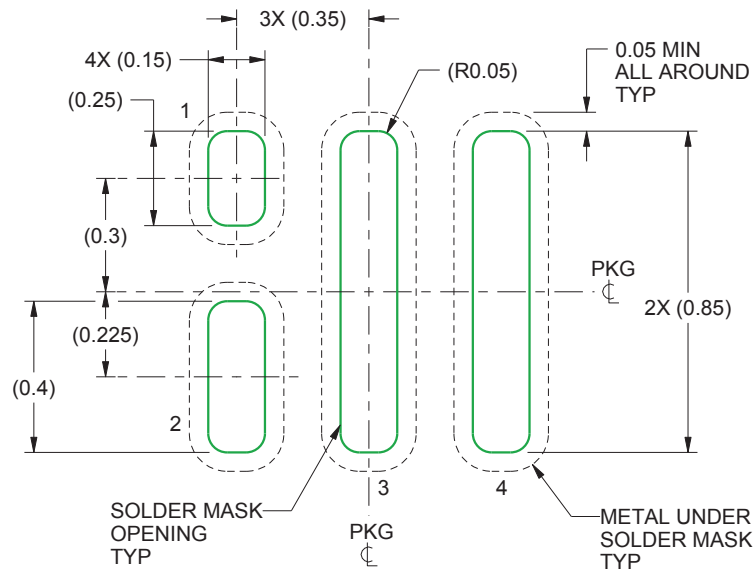
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This package is a lead-free bump design. Bump finish may vary. To determine the exact finish, refer to the device data sheet or contact a local TI representative.

**Table 1. Pin Configuration Table**

POSITION	DESIGNATION
1	Gate
2	Drain
3	Source
4	Drain

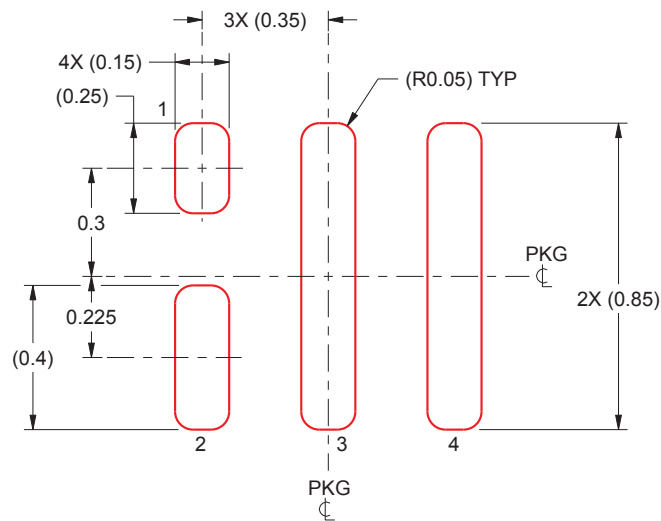


## 7.2 Land Pattern Recommendation



NOTE: For more information, see [QFN/SON PCB Attachment](#) (SLUA271).

## 7.3 Stencil Recommendation



NOTE: Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

For recommended circuit layout for PCB designs, see [Reducing Ringing Through PCB Layout Techniques](#) (SLPA005).

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD22205L	PREVIEW	PICOSTAR	YMG	4	3000	TBD	Call TI	Call TI	-55 to 150	205	
CSD22205LT	PREVIEW	PICOSTAR	YMG	4	250	TBD	Call TI	Call TI	-55 to 150	205	

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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